

isc Silicon NPN Power Transistor

2SD5011

DESCRIPTION

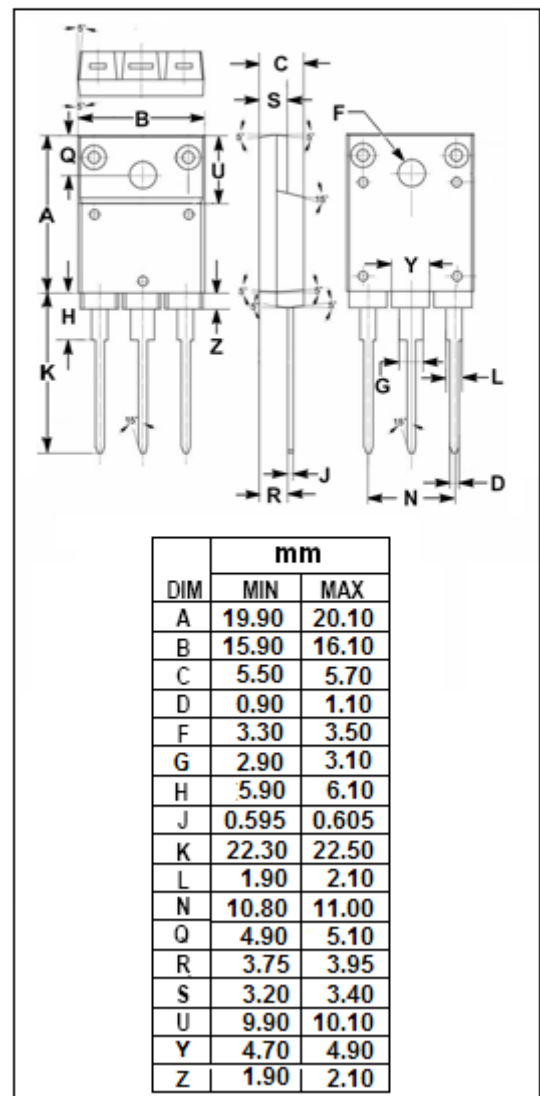
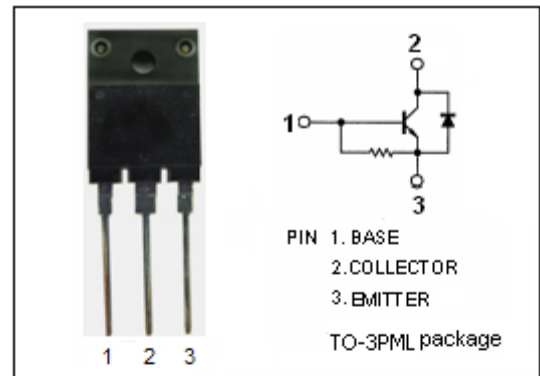
- High Breakdown Voltage-
: $V_{CBO}= 1500V$ (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

APPLICATIONS

- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	3.5	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SD5011****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 2.5A; I_B= 0.8A$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 2.5A; I_B= 0.8A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 800V ; I_E= 0$			10	μ A
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 4V ; I_C= 0$	40		130	mA
h_{FE}	DC Current Gain	$I_C= 0.5A; V_{CE}= 5V$	8			
V_{ECF}	C-E Diode Forward Voltage	$I_F= 3.5A$			2.0	V
f_T	Current-Gain—Bandwidth Product	$I_C= 0.5A; V_{CE}= 10V$		3		MHz
t_f	Fall Time	$I_C= 3A, I_{B1}= 0.8A; I_{B2}= -1.6A$ $R_L= 66.7 \Omega; V_{CC}= 200V$			0.4	μ s